CBRHDSH1-90
CBRHDSH1-100

HIGH DENSITY
1.0 AMP DUAL IN LINE
SCHOTTKY BRIDGE RECTIFIER

Central™
Semiconductor Corp.

HD DIP CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH1-90 and CBRHDSH1-100 are full wave bridge rectifiers in a durable epoxy surface mount molded case, designed for low voltage full wave rectification applications. The molding compound used in this device has UL flammability classification 94V-O.

FEATURES:

- Low Leakage Current, 100nA (TYP) @ V_{RRM}
- Efficient Low Forward Voltage Drop Schottky Diodes
- High 1.0A current rating
- Pb-free plating
- RoHS compliant

MARKING CODE:
CBRHDSH1-90: CSH109
CBRHDSH1-100: CSH110

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL	CBRHDSH1-90	CBRHDSH1-100	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	90	100	V
DC Blocking Voltage	V_R	90	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	63	71	V
Average Forward Current	I_O	1.0		A
Peak Forward Surge Current	I_{FSM}	20		A
Power Dissipation	P_D	1.2		W
Operating Junction Temperature Range	T_J	-50 to +125		°C
Storage Temperature Range	T_{stg}	-50 to +150		°C
Thermal Resistance	Θ_{JA}	85		°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	V_R=V_{RRM}		0.1	10	μA
I_R	V_R=V_{RRM}, T_A=100°C			20	mA
BV_R	I_R=150μA (CBRHDSH1-90)	90			V
BV_R	I_R=150μA (CBRHDSH1-100)	100			V
V_F	I_F=500mA		650	700	mV
V_F	I_F=1.0A		700	750	mV
C_J	V_R=4.0V, f=1.0MHz		230		pF

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PRELIMINARY

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CBRHDSH1-100

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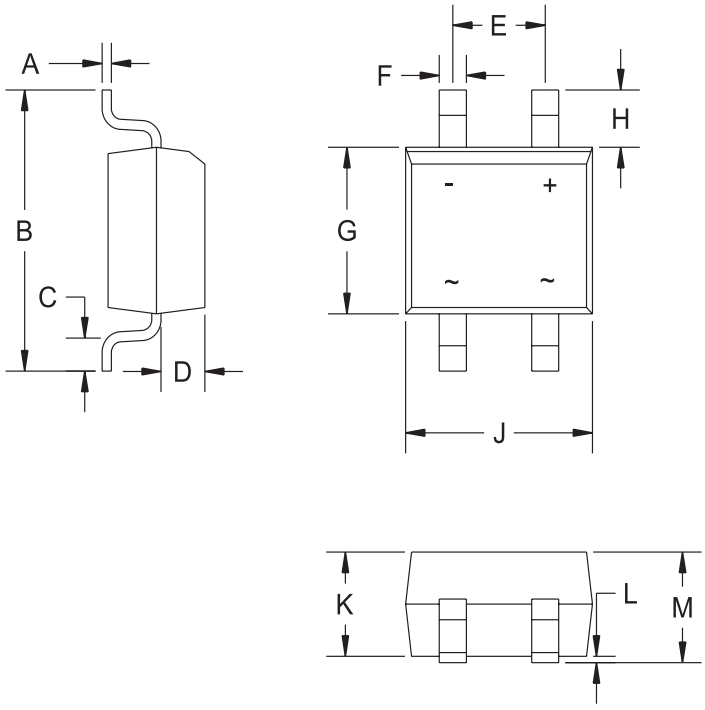
1.0 AMP DUAL IN LINE
SCHOTTKY BRIDGE RECTIFIER

HD DIP CASE - MECHANICAL OUTLINE



R1

MARKING CODE:
CBRHDSH1-90: CSH109
CBRHDSH1-100: CSH110

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.276	-	7.00
C	0.028	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.091	0.106	2.30	2.70
F	0.020	0.031	0.50	0.80
G	0.142	0.157	3.60	4.00
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.091	0.106	2.30	2.70
L	-	0.008	-	0.20
M	-	0.118	-	3.00

HD DIP (REV: R1)

R0 (20-October 2006)